

Abstract

The present invention is directed to a sputtering target which inhibits formation of nodules during sputtering so as to form a transparent conductive film, thereby reliably forming the film, and to a transparent conductive film exhibiting excellent etching processability. The sputtering target is formed of a specific sintered metal oxide product composed of indium oxide, gallium oxide, and zinc oxide (1) or a specific sintered metal oxide product composed of indium oxide, gallium oxide, and germanium oxide (2).



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